

# PBSS5320T-Q

# 20 V, 3 A PNP low VCEsat transistor

21 June 2022

**Product data sheet** 

### 1. General description

PNP low  $V_{CEsat}$  transistor in in a small SOT23 (TO-236AB) Surface-Mounted Device (SMD) plastic package.

NPN complement: PBSS4320T

### 2. Features and benefits

- Low collector-emitter saturation voltage V<sub>CEsat</sub> and corresponding low R<sub>CEsat</sub>
- · High collector current capability
- · High collector current gain
- Improved efficiency due to reduced heat generation
- Qualified according to AEC-Q101 and recommended for use in automotive applications

## 3. Applications

- · Power management applications
- Low and medium power DC/DC convertors
- · Supply line switching
- · Battery chargers
- · Linear voltage regulation with low voltage drop-out (LDO).

#### 4. Quick reference data

#### Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>CEO</sub>	collector-emitter voltage	open base	-	-	-20	V
I <sub>C</sub>	collector current		-	-	-2	Α
I <sub>CRM</sub>		$\delta \leq 0.25$ ; Operated under pulsed conditions; $t_p \leq 100$ ms	-	-	-3	Α
R <sub>CEsat</sub>	collector-emitter saturation resistance	$I_C$ = -2 A; $I_B$ = -200 mA; pulsed; $t_p$ ≤ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	-	75	105	mΩ



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# 5. Pinning information

#### **Table 2. Pinning information**

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	В	base	]3	
2	Е	emitter		C
3	С	collector		В
			SOT23	   E   sym132

### 6. Ordering information

#### **Table 3. Ordering information**

Type number	Package				
	Name	Description	Version		
PBSS5320T-Q	SOT23	plastic, surface-mounted package; 3 terminals; 1.9 mm pitch; 2.9 mm x 1.3 mm x 1 mm body	SOT23		

### 7. Marking

#### Table 4. Marking codes

Type number	Marking code[1]
PBSS5320T-Q	ZH%

<sup>[1] % =</sup> placeholder for manufacturing site code

# 8. Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>CBO</sub>	collector-base voltage	open emitter		-	-20	V
V <sub>CEO</sub>	collector-emitter voltage	open base		-	-20	V
V <sub>EBO</sub>	emitter-base voltage	open collector		-	-5	V
I <sub>C</sub>	collector current			-	-2	Α
I <sub>CRM</sub>	repetitive peak collector current	$\delta \leq 0.25$ ; Operated under pulsed conditions; $t_p \leq 100 \text{ ms}$		-	-3	А
I <sub>CM</sub>	peak collector current	single pulse; t <sub>p</sub> ≤ 1 ms		-	-5	Α
I <sub>B</sub>	base current			-	-0.5	А
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	[1]	-	300	mW
			[2]	-	480	mW
			[3]	-	540	mW
			[1] [4]	-	1.2	W
Tj	junction temperature			-	150	°C
T <sub>amb</sub>	ambient temperature			-65	150	°C

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Symbol	Parameter	Conditions	Min	Max	Unit
$T_{stg}$	storage temperature		-65	150	°C

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm<sup>2</sup>
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm<sup>2</sup>.
- [4] Operated under pulsed conditions: pulse width  $t_p \le 100$  ms; duty cycle  $\delta \le 0.25$ .

#### 9. Thermal characteristics

#### **Table 6. Thermal characteristics**

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R <sub>th(j-a)</sub> thermal resistance from junction to ambient		[1]	-	-	417	K/W	
		[2]	-	-	260	K/W	
		[3]	-	-	230	K/W	
		[1] [4]	-	-	104	K/W	

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm<sup>2</sup>
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm<sup>2</sup>.
- [4] Operated under pulsed conditions: pulse width  $t_p \le 100$  ms; duty cycle  $\delta \le 0.25$ .

### 10. Characteristics

**Table 7. Characteristics** 

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I <sub>CBO</sub>	collector-base cut-off	$V_{CB} = -20 \text{ V}; I_{E} = 0 \text{ A}; T_{amb} = 25 ^{\circ}\text{C}$	-	-	-100	nA
	current	$V_{CB} = -20 \text{ V}; I_E = 0 \text{ A}; T_j = 150 \text{ °C}$	-	-	-50	μA
I <sub>EBO</sub>	emitter-base cut-off current	$V_{EB} = -5 \text{ V}; I_{C} = 0 \text{ A}; T_{amb} = 25 \text{ °C}$	-	-	-100	nA
h <sub>FE</sub>	DC current gain	$V_{CE}$ = -2 V; $I_{C}$ = -100 mA; $T_{amb}$ = 25 °C	220	-	-	
		$V_{CE} = -2 \text{ V}; I_{C} = -500 \text{ mA}; T_{amb} = 25 ^{\circ}\text{C}$	220	-	-	
		$V_{CE}$ = -2 V; $I_{C}$ = -1 A; pulsed; $t_{p}$ ≤ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	200	-	-	
		$V_{CE}$ = -2 V; $I_{C}$ = -2 A; pulsed; $t_{p}$ ≤ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	150	-	-	
		$V_{CE}$ = -2 V; $I_{C}$ = -3 A; pulsed; $t_{p}$ ≤ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	100	-	-	
V <sub>CEsat</sub>	collector-emitter saturation voltage	I <sub>C</sub> = -500 mA; I <sub>B</sub> = -50 mA; T <sub>amb</sub> = 25 °C	-	-	-70	mV
		I <sub>C</sub> = -1 A; I <sub>B</sub> = -50 mA; T <sub>amb</sub> = 25 °C	-	-	-130	mV
		$I_C$ = -2 A; $I_B$ = -100 mA; pulsed; $t_p$ ≤ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	-	-	-230	mV
		$I_C$ = -2 A; $I_B$ = -200 mA; pulsed; $t_p$ ≤ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	-	-	-210	mV
		$I_C$ = -3 A; $I_B$ = -300 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	-	-	-300	mV
R <sub>CEsat</sub>	collector-emitter saturation resistance	$I_C$ = -2 A; $I_B$ = -200 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	-	75	105	mΩ
$V_{BEsat}$	base-emitter saturation voltage	$I_C$ = -2 A; $I_B$ = -100 mA; pulsed; $t_p$ ≤ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	-	-	-1.1	V
		$I_C$ = -3 A; $I_B$ = -300 mA; pulsed; $t_p$ ≤ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	-	-	-1.2	V

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{BEon}$	base-emitter turn-on voltage	$V_{CE}$ = -2 V; $I_{C}$ = -1 A; pulsed; $t_{p}$ ≤ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	-1.2	-	-	V
f <sub>T</sub>	transition frequency	$V_{CE}$ = -5 V; $I_{C}$ = -100 mA; f = 100 MHz; $T_{amb}$ = 25 °C	100	-	-	MHz
C <sub>c</sub>	collector capacitance	$V_{CB}$ = -10 V; $I_E$ = 0 A; $I_e$ = 0 A; $I_e$ = 1 MHz; $I_{CB}$ = 25 °C	-	-	50	pF

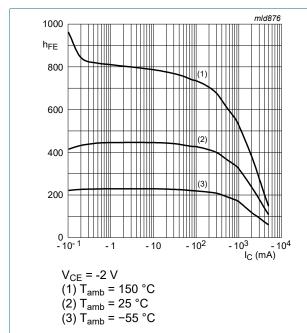


Fig. 1. DC current gain as a function of collector current; typical values

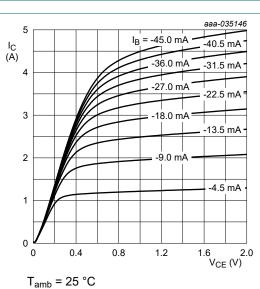
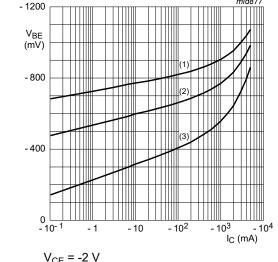


Fig. 2. Collector current as a function of collectoremitter voltage; typical values



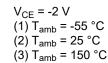
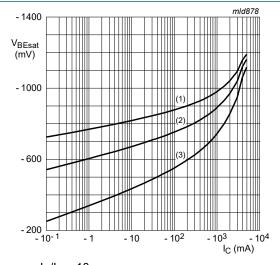


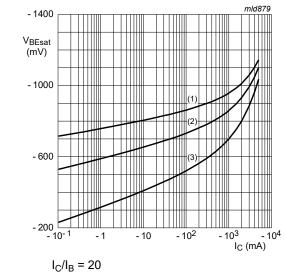
Fig. 3. Base-emitter voltage as a function of collector current; typical values



 $I_C/I_B = 10$ (1)  $T_{amb} = -55$  °C (2)  $T_{amb} = 25$  °C (3)  $T_{amb} = 150$  °C

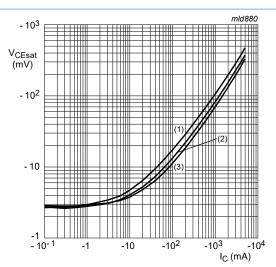
Fig. 4. Base-emitter saturation voltage as a function of collector current; typical values

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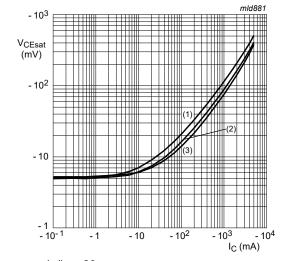
(1) T<sub>amb</sub> = -55 °C (2) T<sub>amb</sub> = 25 °C (3) T<sub>amb</sub> = 150 °C

Fig. 5. Base-emitter saturation voltage as a function of Fig. 6. collector current; typical values



$$\begin{split} &I_{\text{C}}/I_{\text{B}} = 10\\ &(1)~T_{\text{amb}} = 150~^{\circ}\text{C}\\ &(2)~T_{\text{amb}} = 25~^{\circ}\text{C}\\ &(3)~T_{\text{amb}} = -55~^{\circ}\text{C} \end{split}$$

Collector-emitter saturation voltage as a function of collector current; typical values



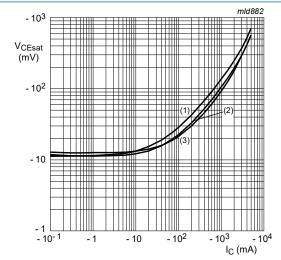
 $I_{\rm C}/I_{\rm B}=20$ 

 $(1) T_{amb} = 150 °C$ 

(2)  $T_{amb} = 25 \, ^{\circ}C$ 

(3)  $T_{amb} = -55 \, ^{\circ}C$ 

Collector-emitter saturation voltage as a Fig. 7. function of collector current; typical values



 $I_{\rm C}/I_{\rm B} = 50$ 

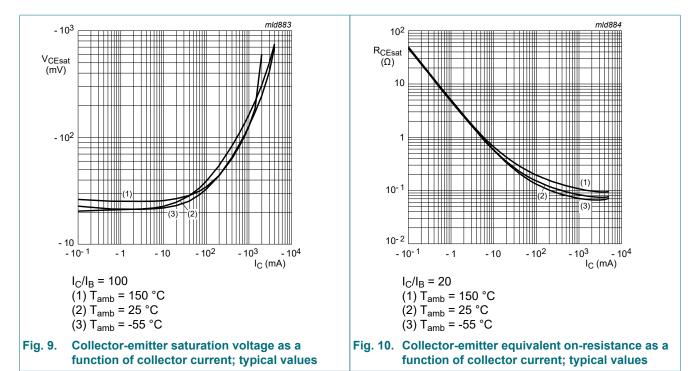
(1)  $T_{amb} = 150 \, ^{\circ}C$ 

(2)  $T_{amb} = 25 \, ^{\circ}C$ 

(3)  $T_{amb} = -55 \, ^{\circ}C$ 

Fig. 8. Collector-emitter saturation voltage as a function of collector current; typical values

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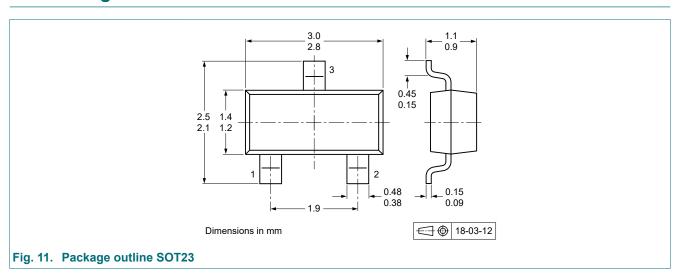


### 11. Test information

### **Quality information**

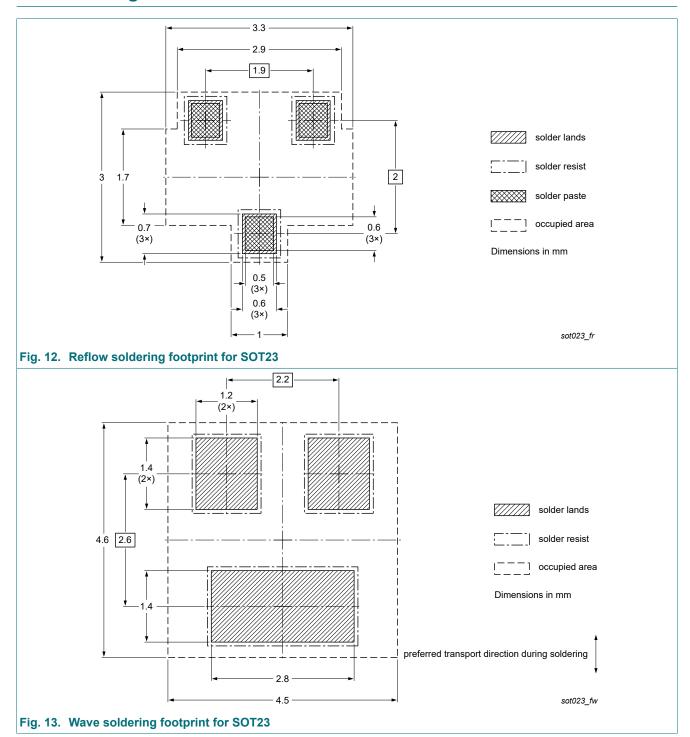
This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

### 12. Package outline



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# 13. Soldering



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# 14. Revision history

#### **Table 8. Revision history**

- Later of the transfer of the							
Data sheet ID	Release date	Data sheet status	Change notice	Supersedes			
PBSS5320T-Q v.2	20220621	Product data sheet	-	PBSS5320T-Q v.1			
Modifications:	Characteristics: Figu	Characteristics: Figure 2 added					
PBSS5320T-Q v.1	20220505	Product data sheet	-	-			

### 20 V, 3 A PNP low VCEsat transistor

### 15. Legal information

#### **Data sheet status**

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- Please consult the most recently issued document before initiating or completing a design.
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